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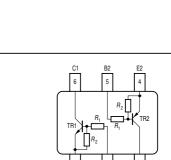


## **NPN/PNP Silicon Digital Transistor Array**

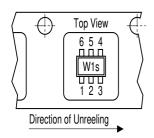
- Switching circuit, inverter, interface circuit, driver circuit
- Two (galvanic) internal isolated NPN/PNP Transistors in one package
- Built in bias resistor NPN and PNP
  (R<sub>1</sub>=10 kΩ, R<sub>2</sub>=47 kΩ)
- Pb-free (ROHS compliant) package
- Qualified according AEC Q101







#### Tape loading orientation



Marking on SOT-363 package (for example W1s) corresponds to pin 1 of device

Position in tape: pin 1 opposite of feed hole side

EHA0719

Type	Marking	Pin Configuration				Package		
BCR35PN V	WUs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

### Maximum Ratings for NPN and PNP Types

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V <sub>CEO</sub>	50	V	
Collector-base voltage	$V_{\mathrm{CBO}}$	50		
Input forward voltage	V <sub>i(fwd)</sub>	40		
Input reverse voltage	V <sub>i(rev)</sub>	6		
DC collector current	/ <sub>C</sub>	100	mA	
Total power dissipation, $T_S$ = 115 °C	P <sub>tot</sub>	250	mW	
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	T <sub>stq</sub>	-65 150		

## Thermal Resistance

Junction - soldering point <sup>1)</sup>	$R_{thJS}$	≤ 140	K/W
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 $<sup>^{1}</sup>$ For calculation of  $R_{\mathrm{thJA}}$  please refer to Application Note AN077 (Thermal Resistance Calculation)



**Electrical Characteristics** at  $T_A$ =25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b> for NPN and PNP Types					
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	50	-	-	V
$I_{\rm C} = 100 \ \mu \text{A}, \ I_{\rm B} = 0$	. ,				
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	50	-	-	
$I_{\rm C}$ = 10 $\mu$ A, $I_{\rm E}$ = 0					
Collector cutoff current	I <sub>CBO</sub>	-	-	100	nA
$V_{\rm CB}$ = 40 V, $I_{\rm E}$ = 0					
Emitter cutoff current	I <sub>EBO</sub>	-	-	167	μΑ
$V_{\rm EB}$ = 6 V, $I_{\rm C}$ = 0					
DC current gain 1)	h <sub>FE</sub>	70	-	-	-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 5 V					
Collector-emitter saturation voltage1)	V <sub>CEsat</sub>	-	-	0.3	V
$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 0.5 mA					
Input off voltage	$V_{i(off)}$	0.5	-	1	
$I_{\rm C}$ = 100 $\mu$ A, $V_{\rm CE}$ = 5 V	, ,				
Input on Voltage	V <sub>i(on)</sub>	0.5	-	1.4	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 0.3 V	, ,				
Input resistor	R <sub>1</sub>	7	10	13	kΩ
Resistor ratio	$R_1/R_2$	0.19	0.21	0.24	-
AC Characteristics for NPN and PNP Types					
Transition frequency	f <sub>T</sub>	-	150	-	MHz
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 5 V, $f$ = 100 MHz					
Collector-base capacitance	C <sub>cb</sub>	-	2	-	pF
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$					

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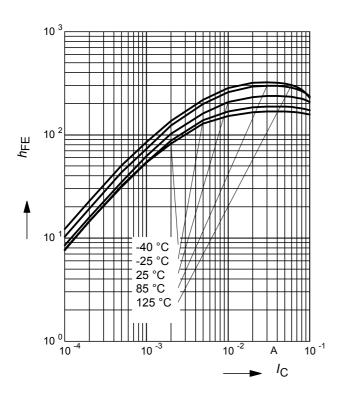
<sup>1)</sup> Pulse test:  $t < 300\mu s$ ; D < 2%



# **NPN Type**

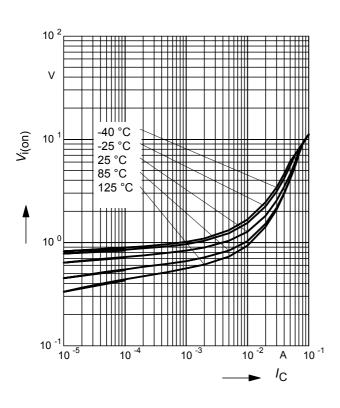
## **DC** Current Gain $h_{FE} = f(I_C)$

 $V_{CF}$  = 5V (common emitter configuration)



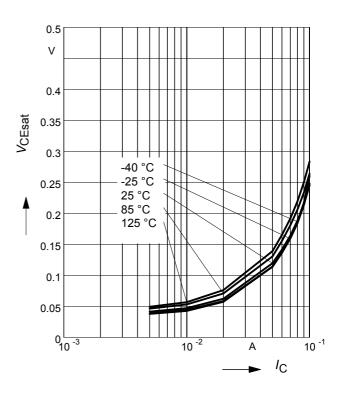
# Input on Voltage $V_{i(On)} = f(I_C)$

 $V_{CE}$  = 0.3V (common emitter configuration)



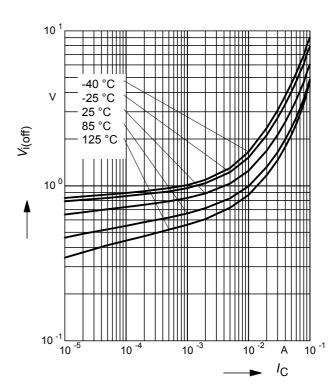
## **Collector-Emitter Saturation Voltage**

 $V_{\text{CEsat}} = f(I_{\text{C}}), h_{\text{FE}} = 20$ 



# Input off voltage $V_{i(Off)} = f(I_C)$

 $V_{CE}$  = 5V (common emitter configuration)

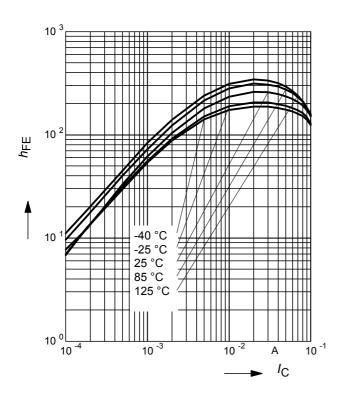




## **PNP Type**

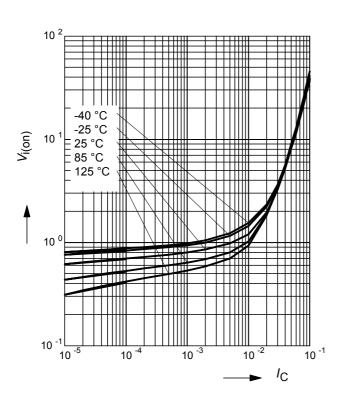
## **DC** Current Gain $h_{FE} = f(I_C)$

 $V_{CF}$  = 5V (common emitter configuration)



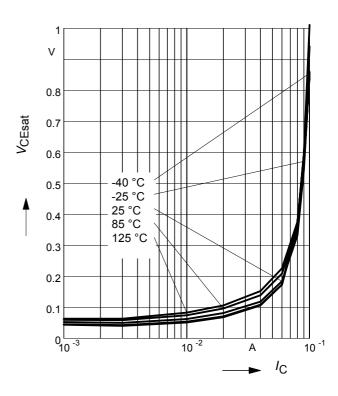
# Input on Voltage $V_{i(On)} = f(I_C)$

 $V_{CE}$  = 0.3V (common emitter configuration)



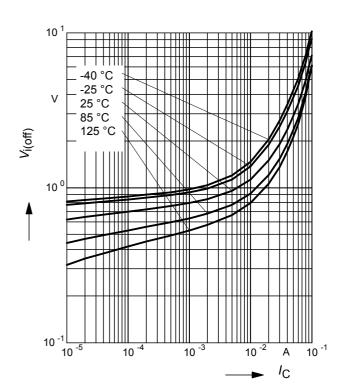
## **Collector-Emitter Saturation Voltage**

 $V_{\text{CEsat}} = f(I_{\text{C}}), h_{\text{FE}} = 20$ 



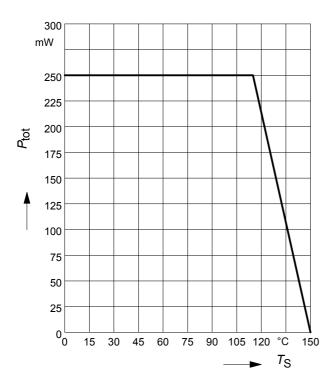
# Input off voltage $V_{i(Off)} = f(I_C)$

 $V_{CE}$  = 5V (common emitter configuration)

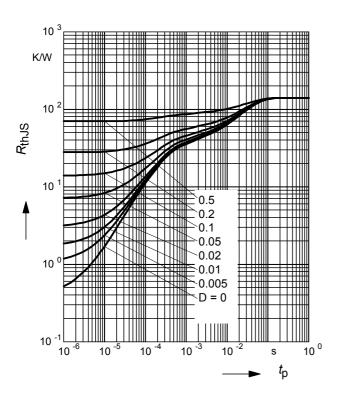




# Total power dissipation $P_{tot} = f(T_S)$

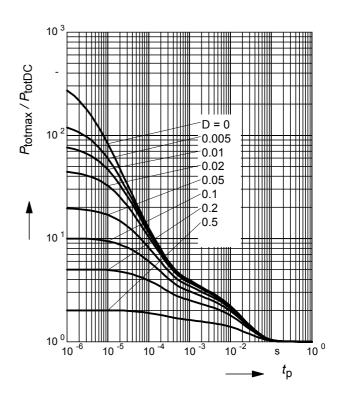


# Permissible Pulse Load $R_{thJS} = f(t_p)$



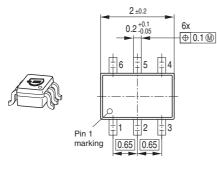
## **Permissible Pulse Load**

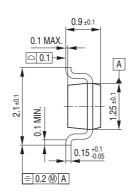
$$P_{\text{totmax}} / P_{\text{totDC}} = f(t_{\text{p}})$$



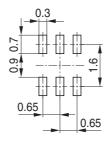


## Package Outline



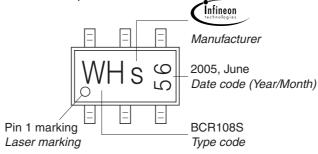


#### Foot Print



## Marking Layout (Example)

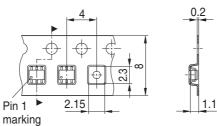
Small variations in positioning of Date code, Type code and Manufacture are possible.



## Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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